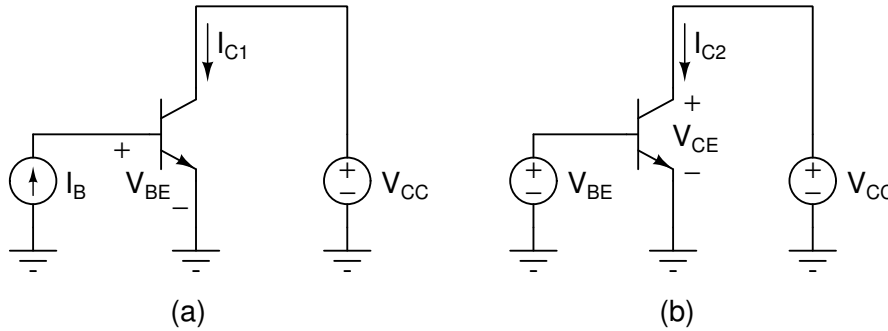


### Part-2(a) (BJT characterization)

3. (a) Take BC547B npn transistor from the LTSPICE library and make a circuit as shown in Fig. 2(a). Use  $V_{CC} = 12\text{ V}$ , sweep  $I_B$  from 0 to 100  $\mu\text{A}$  in step size of 10  $\mu\text{A}$  and plot  $V_{BE}$  with respect to  $I_B$ . What is the forward bias emitter-base junction (EBJ) voltage obtained from the plot? Repeat experiment for  $V_{CC} = 0$  to 12 V in step size of 2 V and give superimposed plots for different  $V_{CC}$  on same graph.  
(Hint: `.dc IB 0 100u 10u VCC 0 12 2`)



**Figure 2**

- (b) Use the schematic shown in Fig. 2(b) in LTSPICE and plot  $I_C$  vs  $V_{BE}$  for  $V_{CC} = 12\text{ V}$  at 20° C, 30° C, 40° C, 50° C by sweeping  $V_{BE}$  from 0 to 0.7 V in step size of 0.01 V. All plots should overlay on same graphical axis.  
(Hint: `.dc VBE 0 0.7 0.01, .step TEMP 20 50 10` or `.step TEMP LIST 20 30 40 50`)
- (c) For Fig. 2(a), plot  $I_C$  vs  $V_{CE}$  by sweeping  $V_{CC}$  from 0 to 12 V in step size of 0.01 V and sweeping  $I_B = 0\text{ }\mu\text{A}$  to 100  $\mu\text{A}$  in step size of 10  $\mu\text{A}$ . Clearly mark cut-off, saturation and active modes in your characteristic plot. Find and tabulate incremental current gain  $\beta = \frac{\Delta I_C}{\Delta I_B}$  in saturation (at  $V_{CE} = 100\text{ mV}$ ) and active (at  $V_{CE} = 600\text{ mV}$ ) modes for  $I_{B1} = 50\text{ }\mu\text{A}$  to  $I_{B1} = 60\text{ }\mu\text{A}$ . Comment on the reason for the difference observed. Tabulate the current gain  $\beta = \frac{I_C}{I_B}$  at  $V_{CE} = 1\text{ V}$  for different values of  $I_B$ . Do you observe Early effect. Estimate the value of early voltage ( $V_A$ ) from your simulations.  
(Hint: `slope at a point = y/x = IC/(VA + VCE)`)
- (d) In your exams, I will ask similar plots for a pnp transistor. Therefore practise and repeat above experiments for pnp transistor also. **(No need to submit this part)**
- (e) **Practise problems:** All solved examples and exercise problems of Chapter-4 (7th edition) of the reference textbook Sedra and Smith. **(No need to submit this part)**

### Part-2(b) (BJT amplifier analysis and design)

4. Fig. 3 shows a common emitter (CE) voltage amplifier. Given that  $V_{CC} = 12\text{ V}$ ,  $C_B = 10\text{ }\mu\text{F}$ ,  $C_C = 10\text{ }\mu\text{F}$ ,  $C_E = 100\text{ }\mu\text{F}$ ,  $R_1 = 18.46\text{ k}\Omega$ ,  $R_2 = 2.24\text{ k}\Omega$ ,  $R_E = 2\text{ k}\Omega$ ,  $R_C = 30.3\text{ k}\Omega$ ,  $R_L = 1\text{ k}\Omega$  and  $v_{in} = V_m \sin(2\pi f_0 t)\text{ V}$ , where  $f_0 = 1\text{ kHz}$ . Implement the given circuit using BC547B (NXP) in LTSPICE and simulate following:

- (a) Draw the DC picture of the given circuit and calculate theoretically  $V_C$ ,  $V_B$ ,  $V_E$ ,  $I_C$  and  $I_B$ . Find the mode of operation of BJT in the given circuit.  
(Hint: For DC picture: AC sources are replaced with its internal resistance and capacitors act as open (why?). In forward active mode,  $V_{BE}$  is fixed ( $\approx 0.7\text{ V}$ ),  $I_C = \beta I_B$ ,  $\beta$  for 547B you know from previous problem.)

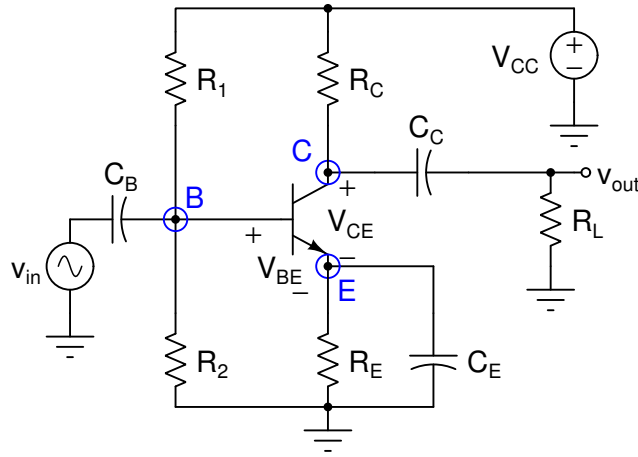


Figure 3

- (b) Run operating point simulation (.op) and verify your theoretical values with the simulated values. Give a table showing theoretical and simulated values of different parameters.
  - (c) Calculate small signal parameters  $g_m$ ,  $r_\pi$  and  $r_o$  for the transistor.
  - (d) Draw the signal picture and small signal equivalent of the circuit.  
(Hint: Capacitors should be replaced by its impedance values at the given frequency.)
  - (e) Derive the expression for the small signal voltage gain ( $A_v = \frac{v_{out}}{v_{in}}$ ).
  - (f) Run transient analysis (.tran 50m) and plot  $v_{in}$  and  $v_{out}$  for  $V_m = 10 \text{ mV}$ . Verify the gain from transient simulations with the calculated gain in the previous part.
  - (g) Plot FFT of  $v_{out}$  and report differences of 2<sup>nd</sup>, 3<sup>rd</sup> and 4<sup>th</sup> harmonics from the fundamental (1 kHz) component.  
(Hint: To plot FFT: on waveform viewer, right click - view - FFT)
  - (h) By using the parametric sweep, vary the amplitude ( $V_m$ ) of the input signal and report total harmonic distortion from the spice error log file. Report corresponding FFT plots also. You might observe that with increasing value of  $V_m$ , THD increases and FFT also shows prominent harmonics. Why does it happen? Briefly comment with supporting calculations.  
(Hint: For parametric sweep: define  $v_{in} = \text{SINE}(0 \{V_m\} 1k)$  (NOTE THAT '{'} is must) and use spice directive .step param Vm 10m 200m 50m. For THD: right click on schematic editor - view - SPICE Error Log. For more details and help refer LTSPICE manual shared earlier.)
  - (i) Run AC analysis (.ac dec 10 1m 1G), plot magnitude and phase of  $A_v = \frac{v_{out}}{v_{in}}$  and report DC gain (dB) and -3 dB bandwidth of the amplifier.  
(Hint: Comment .tran and other analysis, For  $v_{in}$  source in your simulation setup, give  $V_m$  a constant value, give AC amplitude = 1)
  - (j) Now parametrize the resistance  $R_C$  and sweep its value from 28 k $\Omega$  to 40 k $\Omega$  in step size of 2 k $\Omega$  and run ac simulation to plot  $|A_v| = \frac{v_{out}}{v_{in}}$ . Give a table showing DC gain for different values of  $R_C$ ? Why the gain is changing? Compare two cases (30 k $\Omega$  and 40 k $\Omega$ ) quantitatively and justify your answers.
5. Redesign (give values of  $C_B, C_C, C_E, R_1, R_2, R_E, R_C, I_C, I_B$ ) the CE amplifier shown in Fig. 3 to achieve same voltage gain with same  $R_L = 1 \text{ k}\Omega$  and same bandwidth but with reduced supply of 5 V, that is  $V_{CC} = 5 \text{ V}$ . Show design procedure with detailed calculations and report DC, transient and AC simulation results to verify your design. Compare the total DC power ( $P_{DC} = V_{CC} \times I_{Drawn}$ ) consumed for  $V_{CC} = 12 \text{ V}$  and 5 V.